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Customer No.: 31561
Application No.: 10/710,729
Docket No.: 13135-US-PA

5. (original)The LTPS-TFT structure of claim 1, wherein the structure further comprises a gate dielectric layer disposed over the polysilicon film.

6. (original)The LTPS-TFT structure of claim 1, wherein the grain size of the channel region of the polysilicon film is on average greater than the grain size of the source/drain region of the polysilicon film.

Claim 7. (canceled)

8. (original)The LTPS-TFT structure of claim 1, wherein the gate comprises a dual gate structure.

9. (original)The LTPS-TFT structure of claim 1, wherein the structure further comprises:
a dielectric layer disposed on the polysilicon film and the gate, wherein the dielectric layer has a plurality of contact windows that exposes the source/drain region of the polysilicon film; and

a source/drain conductive layer disposed on the dielectric layer, wherein the source/drain conductive layer is electrically connected to the polysilicon film in the source/drain region through the contact window.

Claims 10-13. (canceled)